Product data sheet

1. Product profile

1.1 General description

The BFR520 is an NPN silicon planar epitaxial transistor in a SOT23 plastic package.

1.2 Features and benefits

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

1.3 Applications

- RF front end wideband applications in the GHz range
 - Analog and digital cellular telephones
 - ◆ Cordless telephones (CT1, CT2, DECT, etc.)
 - Radar detectors
 - Pagers and satellite TV tuners (SATV)
 - Repeater amplifiers in fiber-optic systems.

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CBO}	collector-base voltage			-	-	20	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0 \Omega$		-	-	15	V
I _C	collector current (DC)			-	-	70	mA
P _{tot}	total power dissipation	up to T_{sp} = 97 °C	[1]	-	-	300	mW
h _{FE}	DC current gain	$I_C = 20 \text{ mA}; V_{CE} = 6 \text{ V}$		60	120	250	
C _{re}	feedback capacitance	$I_C = I_c = 0 A; V_{CB} = 6 V;$ f = 1 MHz		-	0.4	-	pF
f _T	transition frequency	$I_C = 20 \text{ mA}; V_{CE} = 6 \text{ V};$ f = 1 GHz		-	9	-	GHz
G_UM	maximum unilateral power gain	I_C = 20 mA; V_{CE} = 6 V; T_{amb} = 25 °C					
		f = 900 MHz		-	15	-	dB
		f = 2 GHz		-	9	-	dB



NPN 9 GHz wideband transistor

Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
s ₂₁ ²	insertion power gain	$I_C = 20 \text{ mA}; V_{CE} = 6 \text{ V};$ $T_{amb} = 25 ^{\circ}\text{C};$ f = 900 MHz	13	14	-	dB
NF noise figure	noise figure	$\Gamma_{s} = \Gamma_{opt}$; $T_{amb} = 25 ^{\circ}C$				
		$I_C = 5 \text{ mA}; V_{CE} = 6 \text{ V};$ f = 900 MHz	-	1.1	1.6	dB
		$I_C = 20 \text{ mA}; V_{CE} = 6 \text{ V};$ f = 900 MHz	-	1.6	2.1	dB
		$I_C = 5 \text{ mA}; V_{CE} = 8 \text{ V};$ f = 2 GHz	-	1.9	-	dB

^[1] T_{sp} is the temperature at the soldering point of the collector tab.

2. Pinning information

Table 2. Pinning

	9		
Pin	Description	Simplified outline	Symbol
1	base		_
2	emitter	3	3
3	collector	1 2	1 —
			sym021

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BFR520	-	plastic surface mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking

•	
Type number	Marking code ^[1]
BFR520	32*

^{[1] * =} p: Made in Hong Kong

^{* =} t: Made in Malaysia

^{* =} W: Made in China.

NPN 9 GHz wideband transistor

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	20	V
V _{CES}	collector-emitter voltage	$R_{BE} = 0 \Omega$	-	15	V
V _{EBO}	emitter-base voltage	open collector	-	2.5	V
I _C	collector current (DC)		-	70	mA
P _{tot}	total power dissipation	up to $T_{sp} = 97 ^{\circ}\text{C}$	[1] -	300	mW
T _{stg}	storage temperature		-65	150	°C
Tj	junction temperature		-	175	°C

^[1] T_{sp} is the temperature at the soldering point of the collector tab.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-s)}	thermal resistance from junction to soldering point		<u>11</u> 260	K/W

^[1] T_{sp} is the temperature at the soldering point of the collector tab.

7. Characteristics

Table 7. Characteristics

 $T_j = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector cut-off current	$I_E = 0 A; V_{CB} = 6 V$	-	-	50	nA
h _{FE}	DC current gain	$I_C = 20 \text{ mA}; V_{CE} = 6 \text{ V}$	60	120	250	
C _e	emitter capacitance	$I_C = I_c = 0 A$; $V_{EB} = 0.5 V$; $f = 1 MHz$	-	1	-	pF
C _c	collector capacitance	$I_E = I_e = 0 \text{ A}; V_{CB} = 6 \text{ V};$ f = 1 MHz	-	0.5	-	pF
C_{re}	feedback capacitance	$I_C = 0 A; V_{CB} = 6 V;$ f = 1 MHz	-	0.4	-	pF
f _T	transition frequency	$I_C = 20 \text{ mA}; V_{CE} = 6 \text{ V};$ f = 1 GHz	-	9	-	GHz
G_{UM}	maximum unilateral power	$I_C = 20 \text{ mA}; V_{CE} = 6 \text{ V};$ $T_{amb} = 25 \text{ °C}$	[1]			
	gain	f = 900 MHz	-	15	-	dB
		f = 2 GHz	-	9	-	dB
s ₂₁ ²	insertion power gain	$I_C = 20 \text{ mA}; V_{CE} = 6 \text{ V};$ $T_{amb} = 25 ^{\circ}\text{C}; f = 900 \text{ MHz}$	13	14	-	dB

NPN 9 GHz wideband transistor

Table 7. Characteristics ... continued $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
NF	noise figure	$\Gamma_{\text{s}} = \Gamma_{\text{opt}}; V_{\text{CE}} = 6 \text{ V};$ $T_{\text{amb}} = 25 ^{\circ}\text{C}$				
		$I_C = 5 \text{ mA}$; $f = 900 \text{ MHz}$	-	1.1	1.6	dB
		$I_C = 20 \text{ mA}$; $f = 900 \text{ MHz}$	-	1.6	2.1	dB
		$I_C = 5 \text{ mA}$; $f = 2 \text{ GHz}$	-	1.9	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	I_{C} = 20 mA; V_{CE} = 6 V; R_{L} = 50 Ω ; T_{amb} = 25 °C; f = 900 MHz	-	17	-	dBm
ITO	third order intercept point		[2] -	26	-	dBm

[1] G_{UM} is the maximum unilateral power gain, assuming s_{12} is zero and

$$G_{UM} = 10 \log \frac{|s_{2I}|^2}{(1 - |s_{II}|^2)(1 - |s_{22}|^2)} dB.$$

[2] I_C = 20 mA; V_{CE} = 6 V; R_L = 50 Ω ; T_{amb} = 25 °C; f_p = 900 MHz; f_q = 902 MHz Measured at $f_{(2p-q)}$ = 898 MHz and $f_{(2q-p)}$ = 904 MHz.

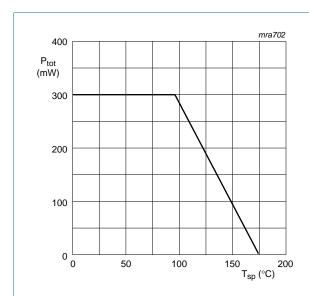
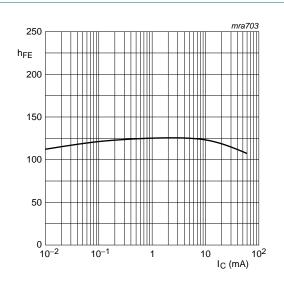


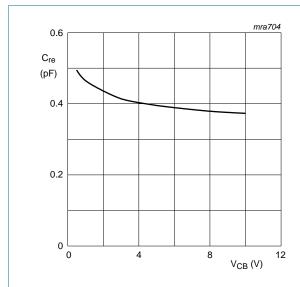
Fig 1. Power derating curve.



 $V_{CE} = 6 V.$

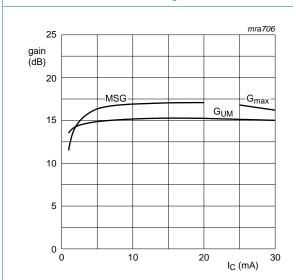
Fig 2. DC current gain as a function of collector current.

NPN 9 GHz wideband transistor



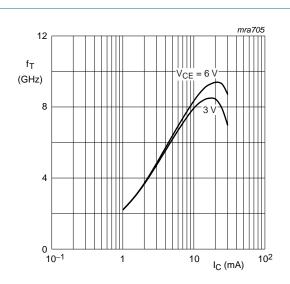
 $I_C = 0 A$; f = 1 MHz.

Fig 3. Feedback capacitance as a function of collector-base voltage.



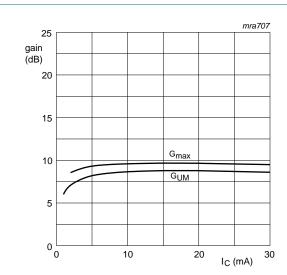
 $V_{CE} = 6 \text{ V}; f = 900 \text{ MHz}.$

Fig 5. Gain as a function of collector current; f = 900 MHz.



 $T_{amb} = 25 \, ^{\circ}C$; $f = 1 \, GHz$.

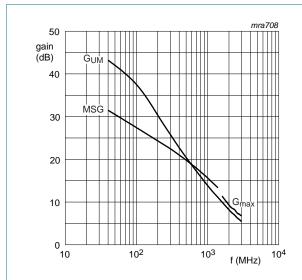
Fig 4. Transition frequency as a function of collector current.



 $V_{CE} = 6 \text{ V}; f = 2 \text{ GHz}.$

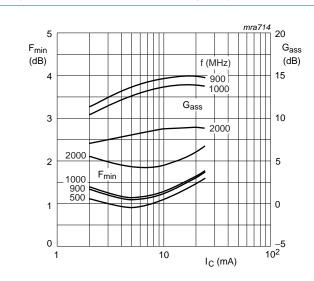
Fig 6. Gain as a function of collector current; f = 2 GHz.

NPN 9 GHz wideband transistor



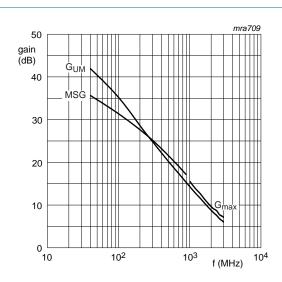
 $V_{CE} = 6 \text{ V}; I_{C} = 5 \text{ mA}.$

Fig 7. Gain as a function of frequency; $I_C = 5$ mA.



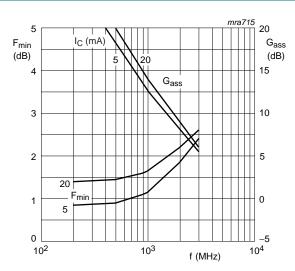
V_{CE} = 6 V.

Fig 9. Minimum noise figure and associated available gain as functions of collector current.



 $V_{CE} = 6 \text{ V}; I_{C} = 20 \text{ mA}.$

Fig 8. Gain as a function of frequency; $I_C = 20$ mA.



 $V_{CE} = 6 V.$

Fig 10. Minimum noise figure and associated available gain as functions of frequency.

NPN 9 GHz wideband transistor

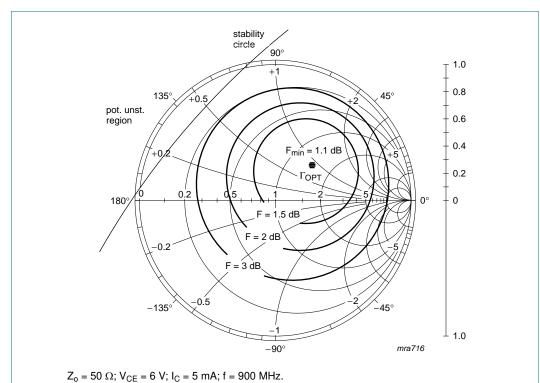


Fig 11. Noise circle figure; f = 900 MHz.

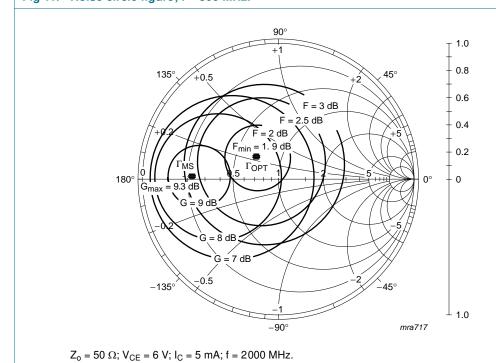


Fig 12. Noise circle figure; f = 2000 MHz.

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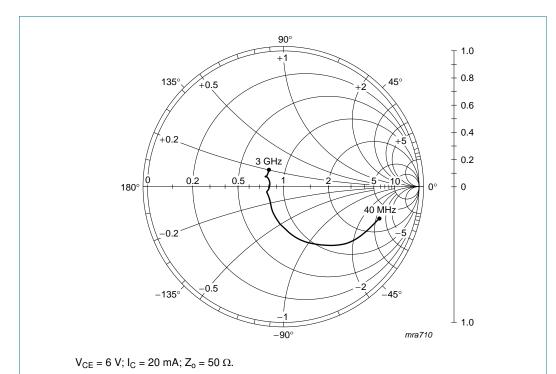
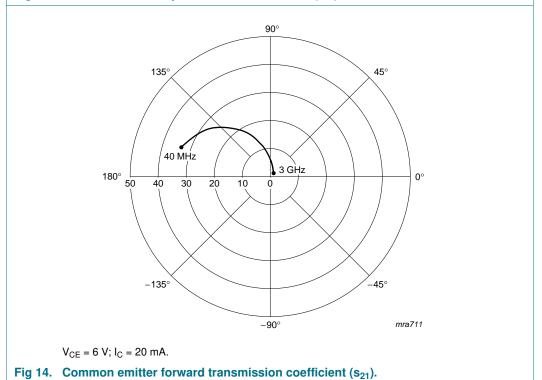


Fig 13. Common emitter input reflection coefficient (s₁₁).



NPN 9 GHz wideband transistor

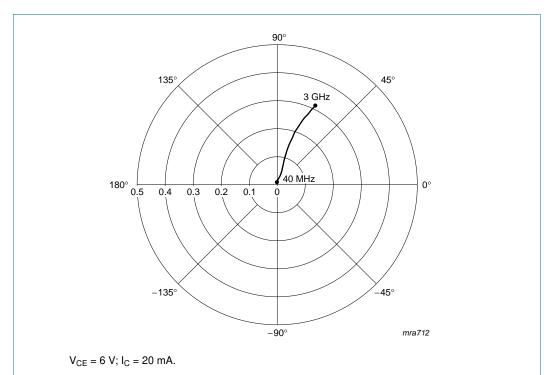
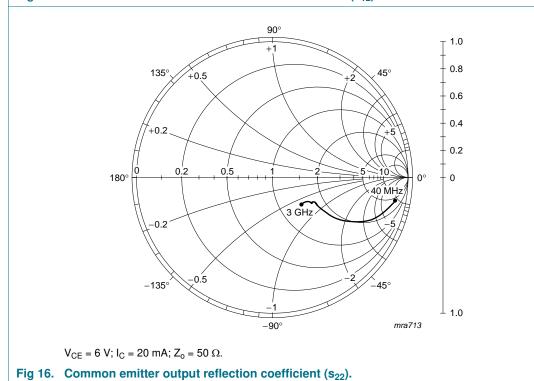


Fig 15. Common emitter reverse transmission coefficient (s₁₂).



NPN 9 GHz wideband transistor

8. Package outline

Plastic surface-mounted package; 3 leads SOT23 В Α Χ = v M A 3 **→** | w (M) B е detail X 0 1 2 **DIMENSIONS (mm are the original dimensions)** UNIT D Ε Q e₁ H_{E} L_p w max. 0.48 0.45 1.1 0.15 3.0 1.4 0.55 0.1 0.9 0.38 0.09 2.8 1.2 0.15 REFERENCES **EUROPEAN** OUTLINE ISSUE DATE VERSION JEDEC **PROJECTION** IEC JEITA -04-11-04 SOT23 TO-236AB 06-03-16

Fig 17. Package outline SOT23 (TO-236AB).

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NPN 9 GHz wideband transistor

9. Revision history

Table 8. Revision history

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BFR520 v.4	20110913	Product data sheet	-	BFR520 v.3
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity
	 Legal texts 	have been adapted to the ne	ew company name whe	ere appropriate.
	 Package or 	utline drawings have been up	odated to the latest vers	sion.
BFR520 v.3 (9397 750 13397)	20040901	Product data sheet	-	BFR520_CNV v.2
BFR520_CNV v.2	19971204	Product specification	-	-

NPN 9 GHz wideband transistor

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BFR520

NPN 9 GHz wideband transistor

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NPN 9 GHz wideband transistor

12. Contents

1	Product profile 1
1.1	General description
1.2	Features and benefits
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information
4	Marking
5	Limiting values
6	Thermal characteristics 3
7	Characteristics 3
8	Package outline
9	Revision history
10	Legal information 12
10.1	Data sheet status
10.2	Definitions
10.3	Disclaimers
10.4	Trademarks13
11	Contact information
12	Contents

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